

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT

In re Application of:

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Group Art Unit: Unknown

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Att'y Docket: 2000.064400/DE0058

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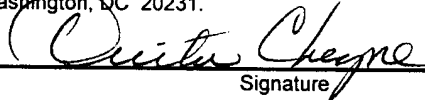
Filed: May 3, 2001

For: METHOD OF FORMING A SUBSTRATE
CONTACT IN A FIELD EFFECT
TRANSISTOR FORMED OVER A
BURIED INSULATOR LAYER

SUBMISSION OF PRIORITY DOCUMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

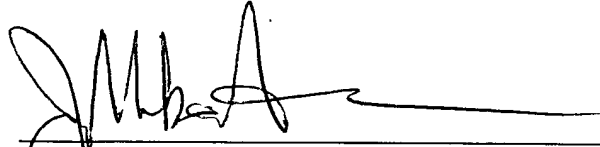
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Transmitted for filing herewith is the certified copy of the priority document – German Patent Application No. 100 54 109.7 filed on October 31, 2000.

If any fees under 37 C.F.R. §§ 1.16 to 1.21 be required for any reason relating to the enclosed materials, the Assistant Commissioner is authorized to said fees Advanced Micro Devices, Inc. Deposit Account No. 01-0365/DE0058.

Please date stamp and return the accompanying postcard to evidence receipt of this document.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'J. Mike Amerson', written over a horizontal line.

Date: May 3, 2001

J. Mike Amerson

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Prioritätsbescheinigung über die Einreichung einer Patentanmeldung

Aktenzeichen: 100 54 109.7

Anmeldetag: 31. Oktober 2000

Anmelder/Inhaber: ADVANCED MICRO DEVICES, INC., Sunnyvale, Calif./US

Bezeichnung: A METHOD OF FORMING A SUBSTRATE CONTACT IN A FIELD EFFECT TRANSISTOR FORMED OVER A BURIED INSULATOR LAYER

IPC: H 01 L 21/336

Die angehefteten Stücke sind eine richtige und genaue Wiedergabe der ursprünglichen Unterlagen dieser Patentanmeldung.

München, den 1. März 2001
Deutsches Patent- und Markenamt
Der Präsident
Im Auftrag

A handwritten signature in black ink, likely belonging to the President of the German Patent and Trademark Office.